

**HALOGEN** FREE

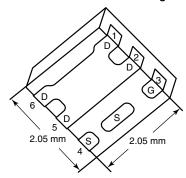


Vishay Siliconix

# P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ ) Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)						
- 20	$0.0165 \text{ at V}_{GS} = -4.5 \text{ V}$	- 12 <sup>a</sup>							
	$0.0185 \text{ at V}_{GS} = -3.7 \text{ V}$	- 12 <sup>a</sup>	23 nC						
	$0.0300$ at $V_{GS} = -2.5 \text{ V}$	- 12 <sup>a</sup>							

#### PowerPAK SC-70-6L-Single



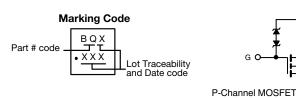
Ordering Information: SiA445EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- 100 %  $\rm R_{\rm g}$  Tested Built in ESD Protection with Zener Diode
- Typical ESD Performance: 2000 V
- Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- Smart Phones, Tablet PCs, Mobile Computing
  - Battery Switch
  - Charger Switch
  - Load Switch



Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	- 20	V	
Gate-Source Voltage		$V_{GS}$	± 12	V	
	T <sub>C</sub> = 25 °C		- 12 <sup>a</sup>		
Continuous Drain Current (T <sub>.I</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I_	- 12 <sup>a</sup>		
Continuous Diain Current (1) = 150 C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 11.8 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		- 9.5 <sup>b, c</sup>	Α	
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	- 50		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	1-	- 12 <sup>a</sup>		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 2.9 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		19		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	D.	12	W	
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.5 <sup>b, c</sup>	VV	
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature R	ange	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperatur	e) <sup>d, e</sup>		260	1	

THERMAL RESISTANCE RATINGS										
Parameter		Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R <sub>th IC</sub>	5.3	6.5	]					

#### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

Document Number: 63619 S11-2525-Rev. A, 26-Dec-11

# SiA445EDJ

# Vishay Siliconix



SPECIFICATIONS (T <sub>J</sub> = 25 °C			M:-	Tim	Mex	11-14
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static  Drain Course Breakdown Valters	l v	V = 0.V L 050 ·· A	00			.,
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V mV/°C
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 13		
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.6		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 0.5		- 1.2	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V			± 60	
	400	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	
	-033	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α
		$V_{GS} = -4.5 \text{ V}, I_D = -7 \text{ A}$		0.0135	0.0165	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -3.7 \text{ V}, I_D = -5 \text{ A}$		0.0150	0.0185	
		$V_{GS} = -2.5 \text{ V}, I_D = -5 \text{ A}$		0.0210	0.0300	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 7 A		29		S
Dynamic <sup>b</sup>				•		
Input Capacitance	C <sub>iss</sub>			2130		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		290		
Reverse Transfer Capacitance	C <sub>rss</sub>			280		
Total Gate Charge	0	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 12 A		48	72	nC
	$Q_g$			23	35	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -12 \text{ A}$		3.1		
Gate-Drain Charge	$Q_{gd}$			6.7		
Gate Resistance	$R_g$	f = 1 MHz	1.2	6	12	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			25	50	
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 10 V, $R_L$ = 1 $\Omega$		25	50	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 9.5 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		55	110	
Fall Time	t <sub>f</sub>			20	40	
Turn-On Delay Time	t <sub>d(on)</sub>			7	15	ns
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 10 V, $R_L$ = 1 $\Omega$		10	20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -9.5 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		60	120	- -
Fall Time	t <sub>f</sub>			17	35	
Drain-Source Body Diode Characteristi					<u> </u>	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 12	
Pulse Diode Forward Current	I <sub>SM</sub>				- 50	Α
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 9.5 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			15	30	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 9.5 A, dl/dt = 100 A/μs,		5	10	nC
Reverse Recovery Fall Time	t <sub>a</sub>			7		
Reverse Recovery Rise Time	t <sub>b</sub>			8		ns

#### Notes:

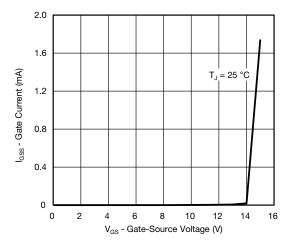
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

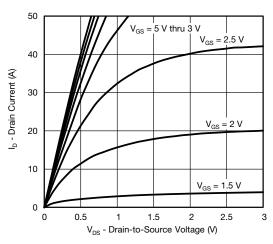


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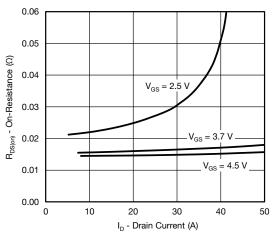
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



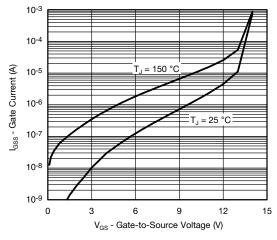
Gate Current vs. Gate-Source Voltage



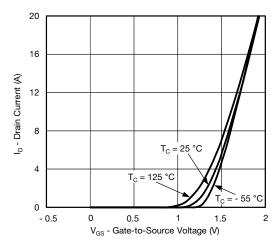
**Output Characteristics** 



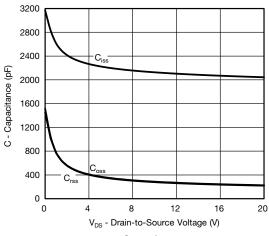
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage



**Transfer Characteristics** 



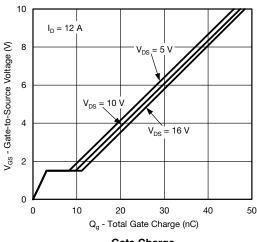
Capacitance

# SiA445EDJ

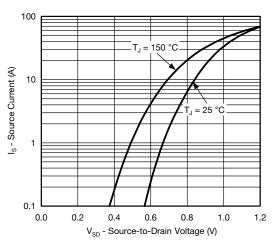
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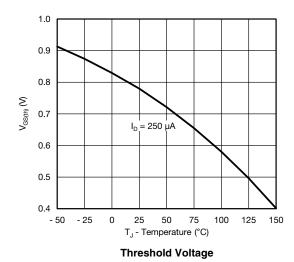
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





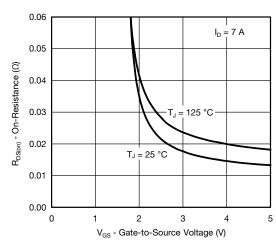


Soure-Drain Diode Forward Voltage

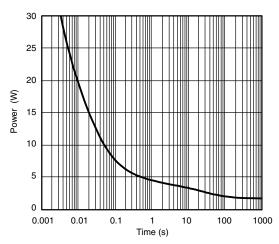


1.5 1.4 R<sub>DS(on)</sub> - On-Resistance (Normalized)  $V_{GS} = 2.5 V$ 1.3 1.2 1.1 1.0 0.9 0.8 0.7 - 50 0 25 50 75 125 150 100 T<sub>J</sub> - Junction Temperature (°C)

On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

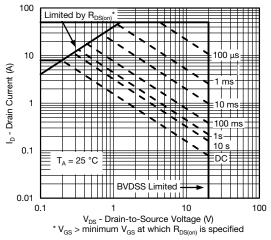


Single Pulse Power, Junction-to-Ambient

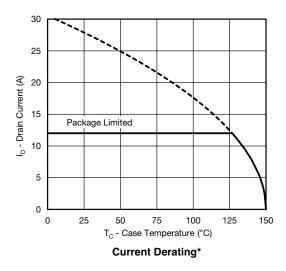


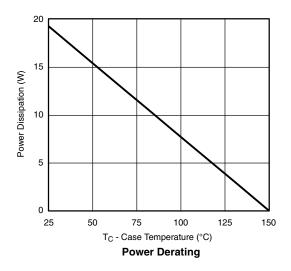
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient





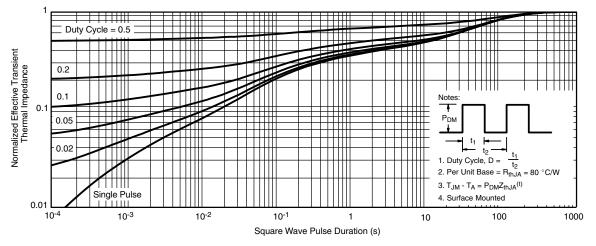
Document Number: 63619 S11-2525-Rev. A, 26-Dec-11

<sup>\*</sup> The power dissipation PD is based on TJ(max) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

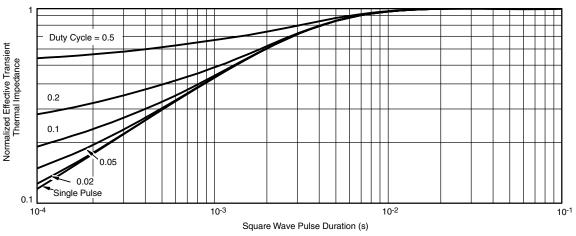
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

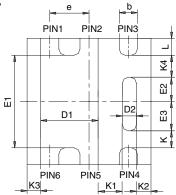
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63619.





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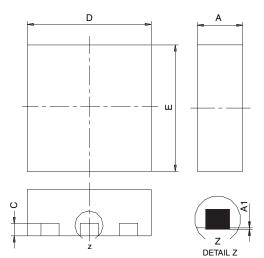
## PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
   Package outline exclusive of mold flash and metal burr
   Package outline inclusive of plating

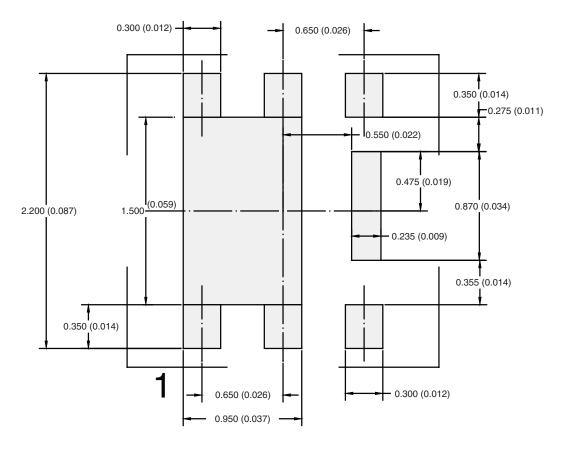
	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
<b>A</b> 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	١		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP 0.009 TYP			0.252 TYP 0.010 TYP				1				
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 - Rev. C. 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Vishay

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Revision: 02-Oct-12 Document Number: 91000

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IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 US6M2GTR TK10A80W,S4X(S SSM6P69NU,LF